2SD2485

Silicon NPN Epitaxial

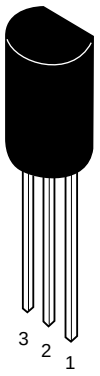
Application

Low frequency power amplifier

Features

- Low saturation voltage
  $V_{CE(sat)}$ = 0.1 V typ. (at I_C = 1 A, I_B = 50 mA)
- Large current capacitance
  I_C = 2 A

TO-92MOD.



1. Emitter
2. Collector
3. Base

Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	80	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Collector peak current	ic(peak)*	3	A
Collector power dissipation	P_C	0.9	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: * PW ≤ 10 ms, duty cycle ≤20 %

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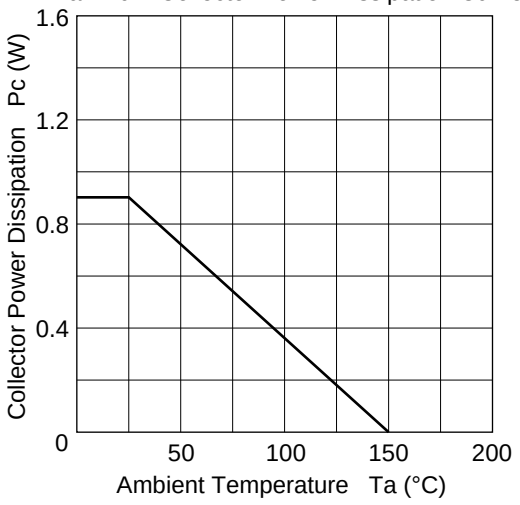
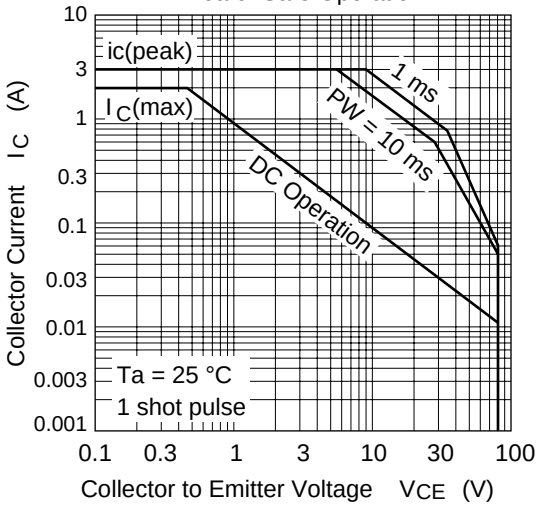
Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	80	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	I_E = 10 µA I_C = 0
Collector to base cutoff current	I_{CBO}	—	—	1.0	µA	V_{CB} = 65 V, I_E = 0
Collector to emitter cutoff current	I_{CEO}	—	—	5.0	µA	V_{CE} = 65 V, R_{BE} = ∞
Emitter to base cutoff current	I_{EBO}	—	—	1.0	µA	V_{EB} = 5 V, I_C = 0
DC current transfer ratio	h_{FE1}	120	—	300		V_{CE} = 2 V, I_C = 0.5 A
DC current transfer ratio	h_{FE2}	40	—	—		V_{CE} = 2 V, I_C = 1.5 A
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.1	0.2	V	I_C =1 A I_B = 50 mA
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.2	V	I_C =1 A I_B = 50 mA

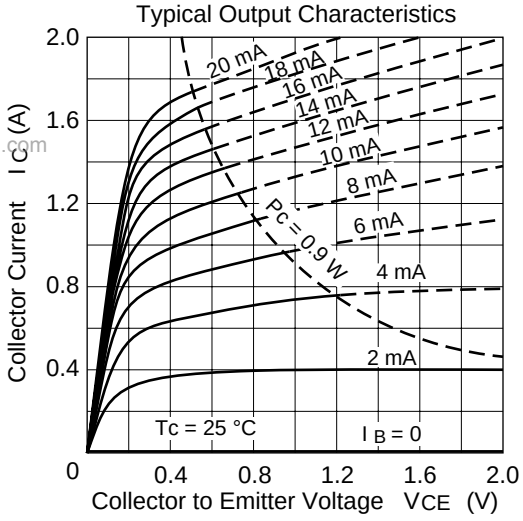
Maximum Collector Power Dissipation Curve



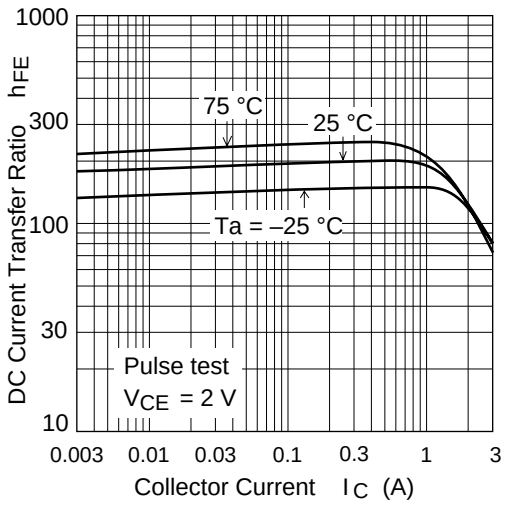
Area of Safe Operation



Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current



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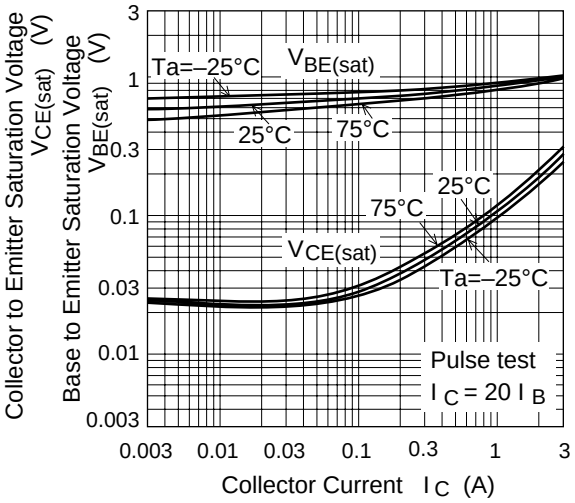
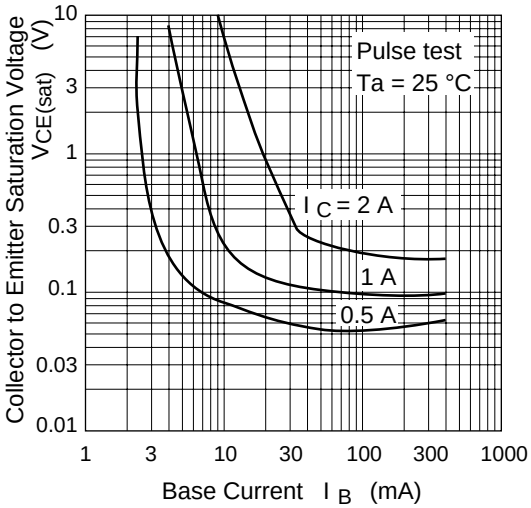
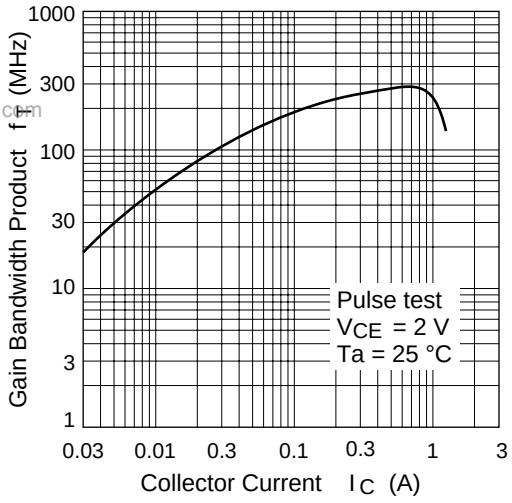
Saturation Voltage vs. Collector Current



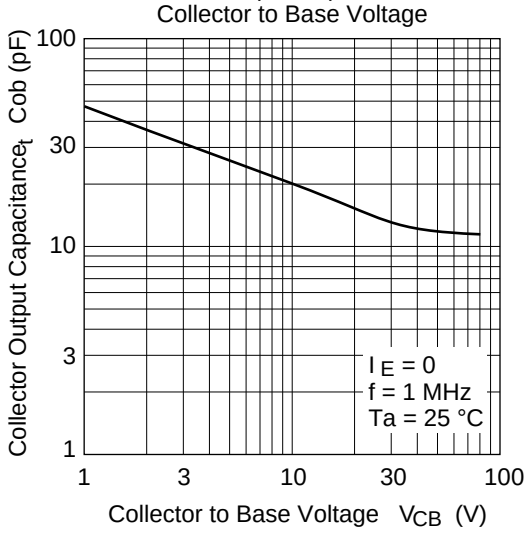
Collector to Emitter Saturation Voltage vs. Base Current



Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage



Typical Transfer Characteristics